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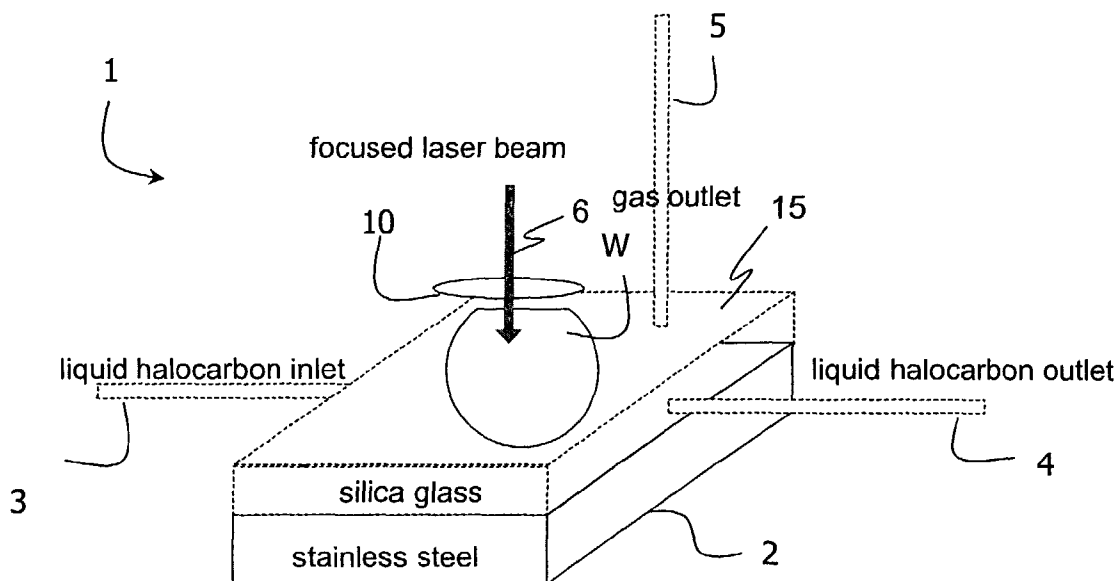
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(54) Title: LASER MACHINING



(57) Abstract: A silicon body W is machined with a UV or green laser beam 6 in a refrigerated liquid halide compound environ-
ment. Local heating with the laser beam of the liquid halide compound in the vicinity of a machining location is sufficient to cause
a chemical reaction between the silicon body and the liquid halide compound which accelerates machining, enhances machining
quality and reduces laser machining generated debris.